



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yeo, *et al.* Docket No.: TSM03-0421
Serial No.: 10/608,287 Art Unit: 2891
Filed: June 27, 2003 Examiner: Chandra Chaudhari
For: Structure and Method for Forming the Gate Electrode in a Multiple-Gate Transistor

Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))

Date of Deposit: June 22, 2005

I hereby certify that the below listed correspondence is being deposited with the United States Postal Service on the date indicated above as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.

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Amendment Transmittal Letter (1 original and 1 copy)
Amendment (19 pages)
Four (4) Replacement Sheets of Figures
Information Disclosure Statement (1 original and 1 copy)
PTO/SB/08A & B with 62 References Cited (4 pages)
Copy of 17 Cited References
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Respectfully submitted,

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